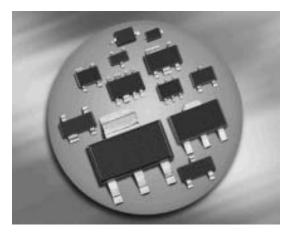


Silicon Variable Capacitance Diode

- For Hyperband TV / VTR tuners, Bd I
- Large capacitance ratio, low series resistance
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101





SD199

Туре	Package	Configuration	L_S (nH)	Marking
SD199E6327	SOD323	single	1.8	red S

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V _R	30	V	
Peak reverse voltage-	V _{RM}	35		
Forward current	I _F	20	mA	
Operating temperature range		-55 150	°C	
Storage temperature	T _{stg}	-55 150		

¹Pb-containing package may be available upon special request



Parameter	Symbol	Values			Unit
		min.	typ.	max.	1
DC Characteristics					
Reverse current	l _R				nA
$V_{R} = 30 \text{ V}$		-	-	10	
$V_{\rm R} = 30$ V, $T_{\rm A} = 85$		-	-	200	
AC Characteristics					
Diode capacitance	CT				pF
$V_{R} = 1 \text{ V}, f = 1 \text{ MHz}$		62	69	76	
$V_{\rm R} = 2 {\rm V}, f = 1 {\rm MHz}$		47	54	62	
$V_{\rm R} = 25 \text{ V}, f = 1 \text{ MHz}$		2.85	3.18	3.6	
$V_{\rm R} = 28 \text{ V}, f = 1 \text{ MHz}$		2.8	3.05	3.3	
Capacitance ratio	C _{T1} /C _{T28}	19.5	22.6	25	-
$V_{\rm R}$ = 1 V, $V_{\rm R}$ = 28 V, f = 1 MHz					
Capacitance ratio	C _{T2} /C _{T25}	15	17	19	7
$V_{\rm R}$ = 2 V, $V_{\rm R}$ = 25 V, f = 1 MHz					
Capacitance matching ¹⁾	$\Delta C_{\rm T}/C_{\rm T}$	-	-	2.5	%
$V_{\rm R}$ = 1 28 V, f = 1 MHz, 8 diodes sequence					
Series resistance	r _S	-	1.15	-	Ω
<i>V</i> _R = 5 V, <i>f</i> = 470 MHz					

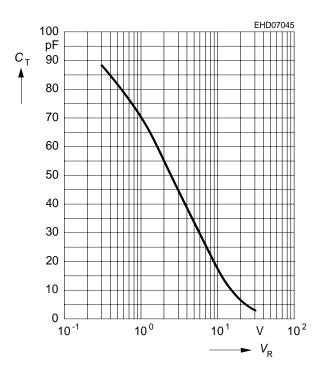
Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

¹For details please refer to Application Note 047.



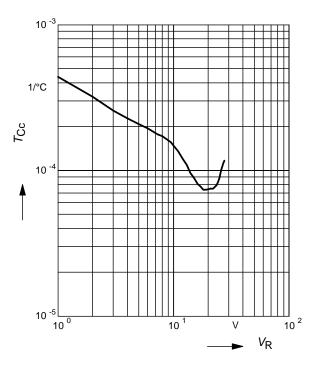
Diode capacitance $C_{T} = f(V_{R})$

f = 1 MHz

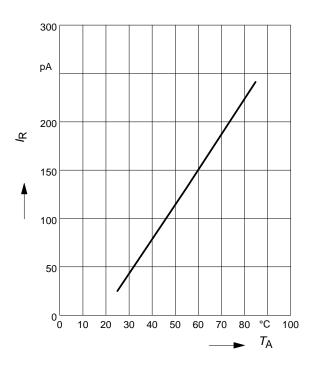


Temperature coefficient of the diode

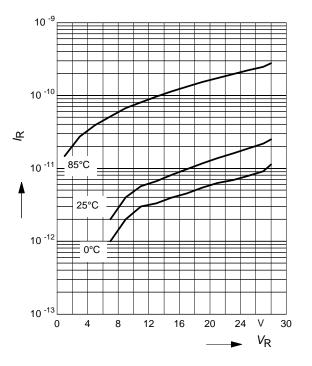
capacitance $T_{Cc} = f(V_R)$



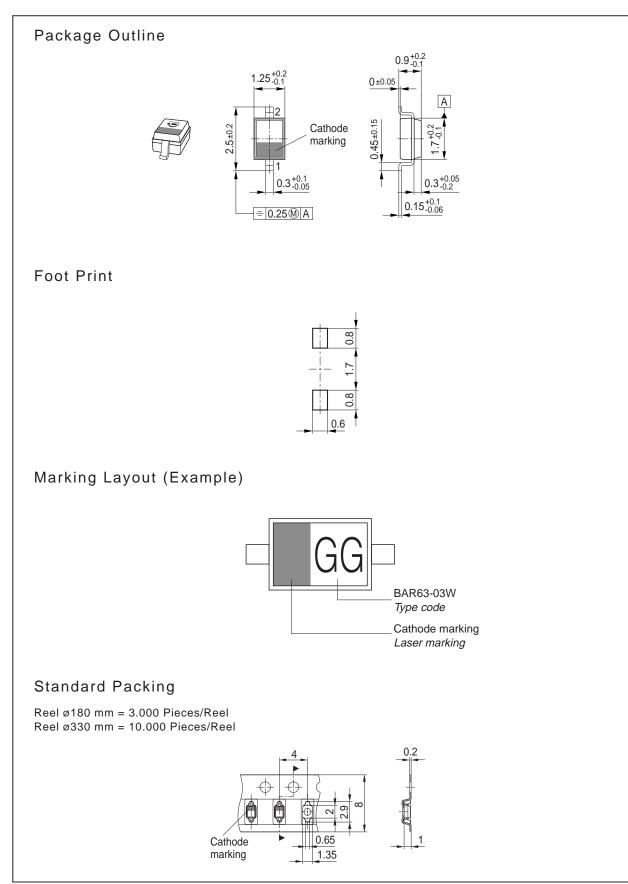
Reverse current $I_{R} = f(T_{A})$ $V_{R} = 28 \text{ V}$



Reverse current $I_{R} = f(V_{R})$ T_{A} = Parameter









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